

PATENT
W&B Docket No.: INF 2070-US
OC Docket No.: INFN/0041
Express Mail No.: EV335472247US

ABSTRACT OF THE DISCLOSURE

The invention relates to a dynamic memory cell which can be selected by means of a selection signal and the content of which can be read out by means of a bit line pair with a first and a second bit line, having a storage capacitor and a first and a second selection transistor, in which case, depending on the selection signal, a first terminal of the storage capacitor can be connected to the first bit line via the first selection transistor and a second terminal of the storage capacitor can be connected to the second bit line via the second selection transistor.